# NST846BF3T5G

# NPN General Purpose Transistor

The NST846BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### Features

- h<sub>FE</sub>, 200–450
- Low  $V_{CE(sat)}$ ,  $\leq 0.25 \text{ V}$
- Reduces Board Space
- This is a Halide–Free Device
- This is a Pb–Free Device

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	65	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	80	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 1)	432	°C/W
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R <sub>ΨJL</sub> (Note 2)	143	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

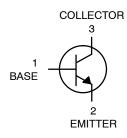
1. 100 mm<sup>2</sup> 1 oz, copper traces.

2. 500 mm<sup>2</sup> 1 oz, copper traces.



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NST846BF3T5G



STYLE 1 (Rotated 90° Clockwise





### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NST846BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## NST846BF3T5G

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

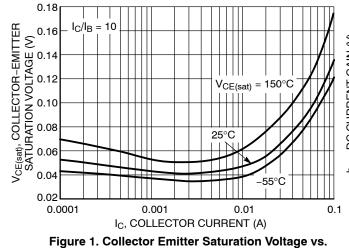
Chara	octeristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage	e (I <sub>C</sub> = 10 mA)	V <sub>(BR)CEO</sub>	65	-	-	V
Collector – Emitter Breakdown Voltage	e (I <sub>C</sub> = 10 μA, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	80	-	-	V
Collector – Base Breakdown Voltage	I <sub>C</sub> = 10 μA)	V <sub>(BR)CBO</sub>	80	-	-	V
Emitter-Base Breakdown Voltage (I <sub>E</sub>	= 1.0 μΑ)	V <sub>(BR)EBO</sub>	6.0	-	-	V
Collector Cutoff Current	(V <sub>CB</sub> = 30 V) (V <sub>CB</sub> = 30 V, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	_		15 5.0	nA μA

#### **ON CHARACTERISTICS**

DC Current Gain ( $I_C = 10 \ \mu A, \ V_{CE} = 5.0 \ V$ ) ( $I_C = 2.0 \ mA, \ V_{CE} = 5.0 \ V$ )	h <sub>FE</sub>	_ 200	150 290	_ 450	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA) (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5.0 mA)	V <sub>CE(sat)</sub>	-	-	0.25 0.6	V
Base – Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA) (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5.0 mA)	V <sub>BE(sat)</sub>	-	0.7 0.9	-	V
Base – Emitter Voltage (I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 V) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V)	V <sub>BE(on)</sub>	580 -	660 -	700 770	mV

#### SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ( $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$ )	f <sub>T</sub>	100	-	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	-	4.5	pF
Input Capacitance ( $V_{EB}$ = 0.5 V, $I_C$ = 0 mA, f = 1.0 MHz)	C <sub>ibo</sub>	-	-	10	pF
Noise Figure (I <sub>C</sub> = 0.2 mA, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 2.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB



Collector Current

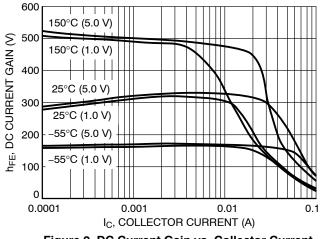
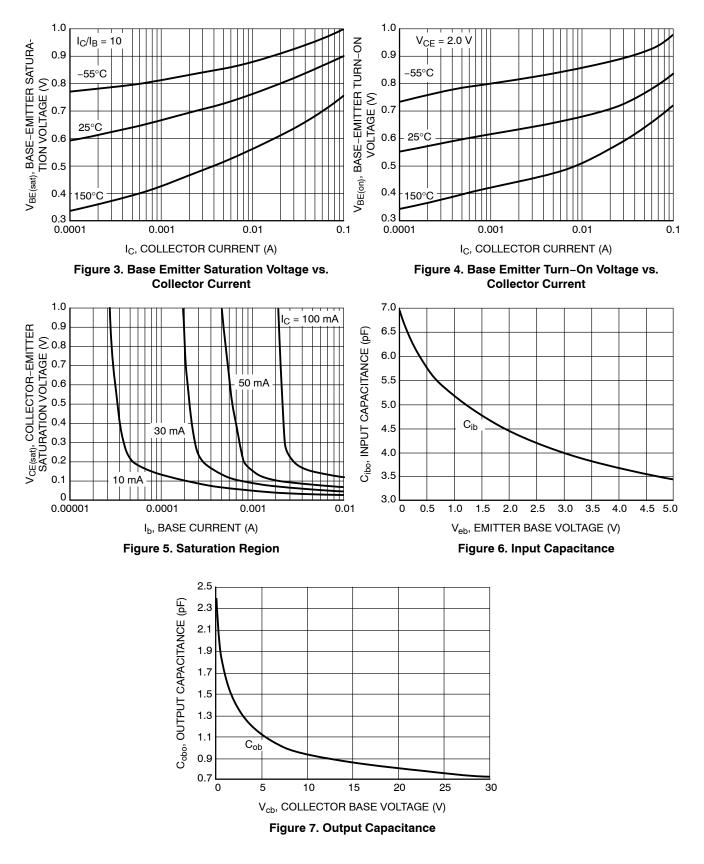


Figure 2. DC Current Gain vs. Collector Current

### NST846BF3T5G



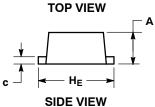




SCALE 8:1



SOT-1123 CASE 524AA ISSUE C





#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

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DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0	.6X0.37, 0.35P	PAGE 1 OF 1
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- CONTROLLING DIMENSION: MILLIMETERS.
   MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.34	0.40		
b	0.15	0.28		
b1	0.10	0.20		
С	0.07 0.17			
D	0.75	0.85		
Е	0.55	0.65		
е	0.35	0.40		
HE	0.95 1.05			
L	0.185 REF			
L2	0.05	0.15		

GENERIC MARKING DIAGRAM\*

X = Specific Device Code M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " •", may or may not be present.

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